



**GreenPAK** ™

## **Enya Button Controller**

### **General Description**

Dialog SLG7RN45753 is a low power and small form device. The SoC is housed in a 1.6mm x 1.6mm STQFN package which is optimal for using with small devices.

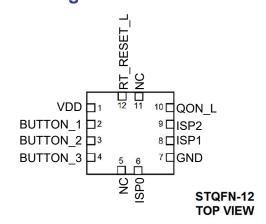
### **Features**

- Low Power Consumption
- Pb Free / RoHS Compliant
- Halogen Free
- STQFN 12 Package

### **Output Summary**

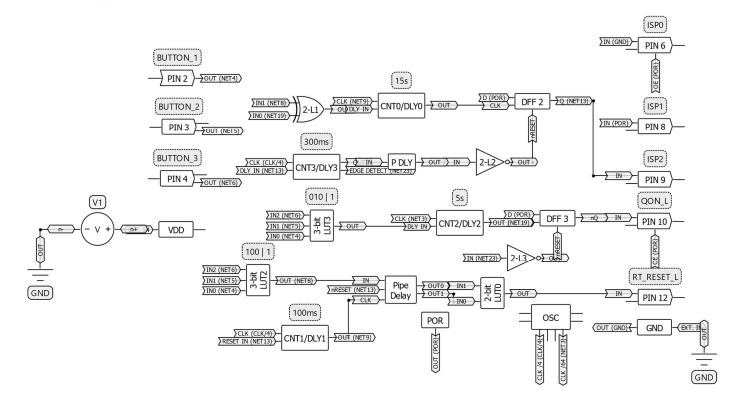
3 Outputs - Open Drain NMOS 1X 2 Outputs - Push Pull 1X

### **Pin Configuration**





### **Block Diagram**





**Pin Configuration** 

Pin#	Pin Name	Pin Name Type Pin Description		Internal Resistor
1	VDD	PWR	Supply Voltage	
2	BUTTON_1	Digital Input	Digital Input without Schmitt trigger	floating
3	BUTTON_2	Digital Input	Digital Input without Schmitt trigger	floating
4	BUTTON_3	Digital Input	Digital Input without Schmitt trigger	floating
5	NC		Keep Floating or Connect to GND	
6	ISP0	Digital Output	Push Pull 1X	floating
7	GND	GND	Ground	
8	ISP1	Digital Output	Open Drain NMOS 1X	floating
9	ISP2	Digital Output	Push Pull 1X	floating
10	QON_L	Digital Output	Open Drain NMOS 1X	floating
11	NC		Keep Floating or Connect to GND	
12	RT_RESET_L	Digital Output	Open Drain NMOS 1X	floating

**Ordering Information** 

Part Number	Package Type					
SLG7RN45753V	V=STQFN-12					
SLG7RN45753VTR	STQFN-12 – Tape and Reel (3k units)					



### **Absolute Maximum Conditions**

Parameter	Min.	Max.	Unit	
Supply Voltage on VDD relative	to GND	-0.5	7	V
DC Input Voltage		GND - 0.5V	VDD + 0.5V	V
Maximum Average or DC Current	Push-Pull 1x		12	mA
(Through pin)				
Current at Input Pin	-1.0	1.0	mA	
Input leakage (Absolute Valu	ne)		1000	nA
Storage Temperature Rang	Storage Temperature Range			
Junction Temperature		150	°C	
ESD Protection (Human Body N	2000		V	
ESD Protection (Charged Device	1000		V	
Moisture Sensitivity Level	•	1		

### **Electrical Characteristics**

Symbol	Parameter	Condition/Note	Min.	Тур.	Max.	Unit
$V_{DD}$	Supply Voltage		2.3	3.3	5.5	V
TA	Operating Temperature		-40	25	125	°C
$C_VDD$	Capacitor Value at VDD			0.1		μF
Cin	Input Capacitance			4		pF
lα	Quiescent Current	Static inputs and floating outputs PIN2, PIN3 and PIN4 are low		7		μA
Vo	Maximal Voltage Applied to any PIN in High-Impedance State				VDD	V
	Maximum Average or DC	T <sub>J</sub> = 85°C			73	mA
IVDD	Current Through VDD Pin (Per chip side, see Note 2)	T <sub>J</sub> = 110°C			35	mA
	Maximum Average or DC	T <sub>J</sub> = 85°C			92	mA
IGND	Current Through GND Pin (Per chip side, see Note 2)	T <sub>J</sub> = 110°C			44	mA
		Logic Input at VDD=1.8V	1.1		VDD	V
ViH	HIGH-Level Input Voltage	Logic Input at VDD=3.3V	1.78		VDD	V
		Logic Input at VDD=5.0V	2.64		VDD	V
		Logic Input at VDD=1.8V	0		0.69	V
VIL	LOW-Level Input Voltage	Logic Input at VDD=3.3V	0		1.21	V
		Logic Input at VDD=5.0V	0		1.84	V
		Push-Pull 1X, I <sub>OH</sub> =100µA, at VDD=1.8V	1.68	1.79		V
Vон	HIGH-Level Output Voltage	Push-Pull 1X, I <sub>OH</sub> =3mA, at VDD=3.3V	2.71	3.09		V
		Push-Pull 1X, I <sub>OH</sub> =5mA, at VDD=5.0V	4.15	4.73		V
		Push-Pull 1X, I <sub>OL</sub> =100µA, at VDD=1.8V		0.02	0.03	V
VoL	LOW-Level Output Voltage	Push-Pull 1X, I <sub>OL</sub> =3mA, at VDD=3.3V		0.18	0.28	V
		Push-Pull 1X, I <sub>OL</sub> =5mA, at VDD=5.0V		0.23	0.33	V



						•
		Open Drain NMOS 1X, I <sub>OL</sub> =100µA, at VDD=1.8V		0.01	0.02	V
		Open Drain NMOS 1X, I <sub>OL</sub> =3mA, at VDD=3.3V		0.09	0.13	V
		Open Drain NMOS 1X, I <sub>OL</sub> =5mA, at VDD=5.0V		0.12	0.16	V
		Push-Pull 1X, V <sub>OH</sub> =VDD- 0.2V, at VDD=1.8V	1.04	1.4		mA
I <sub>OH</sub>	HIGH-Level Output Current (Note 1)	Push-Pull 1X, V <sub>OH</sub> =2.4V, at VDD=3.3V	5.83	10.18		mA
		Push-Pull 1X, V <sub>OH</sub> =2.4V, at VDD=5.0V	21.808	29.1		mA
		Push-Pull 1X, VoL=0.15V, at VDD=1.8V	0.76	1.34		mA
		Push-Pull 1X, V <sub>OL</sub> =0.4V, at VDD=3.3V	4.06	6.44		mA
	Push-Pull 1X, V <sub>OL</sub> =0.4V, at VDD=5.0V		6.01	9.73		mA
loL	(Note 1)	Open Drain NMOS 1X, V <sub>OL</sub> =0.15V, at VDD=1.8V	1.53	2.67		mA
		Open Drain NMOS 1X, VoL=0.4V, at VDD=3.3V	8.13	12.41		mA
		Open Drain NMOS 1X, VoL=0.4V, at VDD=5.0V	11.76	19.46		mA
		At temperature 25°C	14.34	15.02	16.36	s
T <sub>DLY0</sub>	Delay0 Time	At temperature -40 +125°C (Note 3)	13.45	15.02	19.14	s
		At temperature 25°C	4.78	5.01	5.31	s
$T_{DLY2}$	Delay2 Time	At temperature -40 +125°C (Note 3)	4.49	5.01	6.21	s
		At temperature 25°C	286.8	300.1	317.9	ms
T <sub>DLY3</sub>	Delay3 Time	At temperature -40 +125°C (Note 3)	269.1	300.1	372.0	ms
		At temperature 25°C	95.6	99.8	108.3	ms
T <sub>CNT1</sub>	Counter1 Period	At temperature -40 +125°C (Note 3)	89.7	99.8	126.7	ms
Tsu	Startup Time	From VDD rising past 1.35 V		0.27		ms
PON <sub>THR</sub>	Power On Threshold	V <sub>DD</sub> Level Required to Start Up the Chip	1.182	1.346	1.505	V
POFFTHR	Power Off Threshold	V <sub>DD</sub> Level Required to Switch Off the Chip	0.752	0.918	1.11	V

#### Note:

- 1. DC or average current through any pin should not exceed value given in Absolute Maximum Conditions.
- 2. The GreenPAK's power rails are divided in two sides. Pins 2, 3, 4 and 6 are connected to one side, pins 8, 9, 10 and 12 to another.
- 3. Guaranteed by Design.





### **Functionality Waveforms**

D0 - PIN#2 (BUTTON\_1)

D1 - PIN#3 (BUTTON 2)

D2 - PIN#4 (BUTTON\_3)

D3 - PIN#6 (ISP0)

D4 - PIN#8 (ISP1) with external  $5k\Omega$  pull up resistor

D5 - PIN#9 (ISP2)

D6 - PIN#10 (QON\_L) with external  $5k\Omega$  pull up resistor

D7 – PIN#12 (RT\_RESET\_L) with external  $5k\Omega$  pull up resistor

#### 1. The main design functionality for the Power Cycle

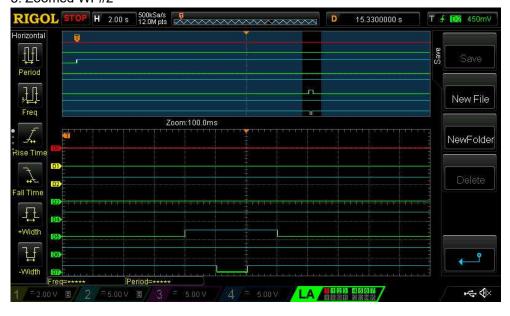




#### 2. The main design functionality for the Serial DFU

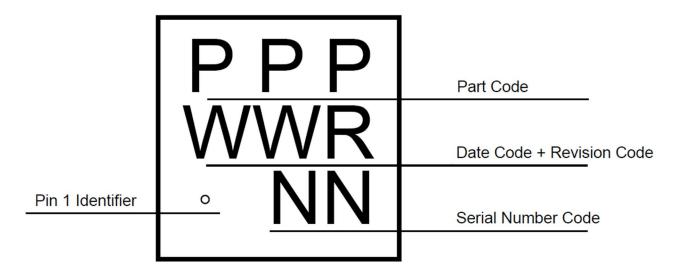


#### 3. Zoomed WF#2





### **Package Top Marking**



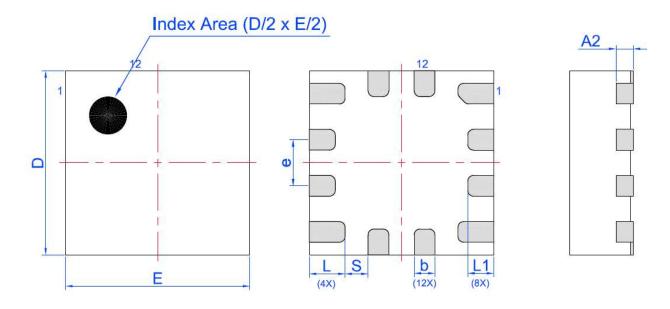
Datasheet Revision	Programming Code Number	Lock Status	Checksum	Part Code	Revision	Date
0.10	001	U	0xC60CCE74			05/06/2022

The IC security bit is locked/set for code security for production unless otherwise specified. The Programming Code Number is not changed based on the choice of locked vs. unlocked status.



### **Package Drawing and Dimensions**

12 Lead STQFN FC Package 1.6 x 1.6 mm IC net weight: 0.0028 g





### Unit: mm

Symbol	Min	Nom.	Max	Symbol	Min	Nom.	Max
Α	0.50	0.55	0.60	D	1.55	1.60	1.65
A1	0.005	-	0.060	E	1.55	1.60	1.65
A2	0.10	0.15	0.20	L	0.26	0.31	0.36
b	0.13	0.18	0.23	L1	0.175	0.225	0.275
е	0.40 BSC			S		0.2 REF	

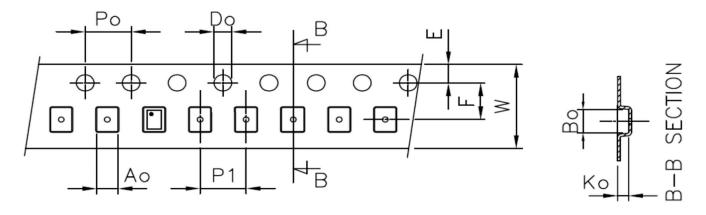


### **Tape and Reel Specification**

		Nominal	Max	Units		Leade	r (min)	Traile	(min)	Таре	Part
Package Type	# of Pins	Package Size [mm]	per Reel	per Box	Reel & Hub Size [mm]	Pockets	Length [mm]	Pockets	Length [mm]	Width [mm]	Pitch [mm]
STQFN 12L FC 0.4P Green	12	1.6x1.6x0.55	3000	3000	178/60	100	400	100	400	8	4

### **Carrier Tape Drawing and Dimensions**

Package Type	Pocket BTM Length	Pocket BTM Width	Pocket Depth	Index Hole Pitch	Pocket Pitch	Index Hole Diameter	Index Hole to Tape Edge	Index Hole to Pocket Center	Tape Width
	A0	В0	K0	P0	P1	D0	Е	F	W
STQFN 12L FC 0.4P Green	1.8±0.05	1.8±0.05	±0.7	4	4	1.5	1.75	3.5	8



### **Recommended Reflow Soldering Profile**

Please see IPC/JEDEC J-STD-020: latest revision for reflow profile based on package volume of 1.408 mm³ (nominal). More information can be found at <a href="https://www.jedec.org">www.jedec.org</a>.

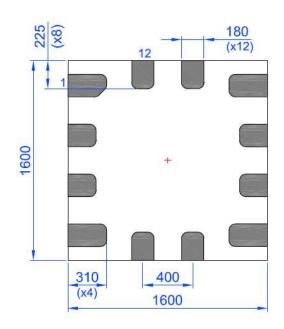


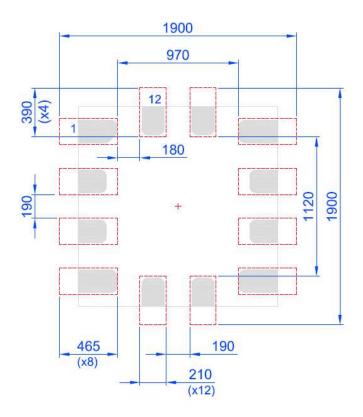
### **Recommended Land Pattern**

Exposed Pad (PKG face down)

Recommended Land Pattern (PKG face down)









**Datasheet Revision History** 

Date	Version	Change
05/06/2022	0.10	New design for SLG46110 chip

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